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May 2014



FCA76N60N

N-Channel SupreMOS® MOSFET

600 V, 76 A, 36 mΩ

Features

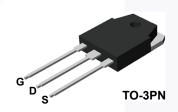
- $R_{DS(on)}$ = 28 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 38 A
- Ultra Low Gate Charge (Typ. Q_g = 218 nC)
- Low Effective Output Capacitance (Typ. C_{oss(eff.)} = 914 pF)
- · 100% Avalanche Tested
- · RoHS Compliant

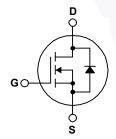
Application

- · Solar Inverter
- · AC-DC Power Supply

Description

The SupreMOS® MOSFET is Fairchild Semiconductor's next generation of high voltage super-junction (SJ) technology employing a deep trench filling process that differentiates it from the conventional SJ MOSFETs. This advanced technology and precise process control provides lowest Rsp on-resistance, superior switching performance and ruggedness. SupreMOS MOSFET is suitable for high frequency switching power converter applications such as PFC, server/telecom power, FPD TV power, ATX power, and industrial power applications.





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter			Unit	
V _{DSS}	Drain to Source Voltage			600	V	
V _{GSS}	Gate to Source Voltage			±30	V	
	Drain Current	- Continuous (T _C = 25°C)		76	А	
ID	Drain Current	- Continuous (T _C = 100°C)	9	48.1	A	
I _{DM}	Drain Current	- Pulsed	- Pulsed (Note 1)		Α	
E _{AS}	Single Pulsed Avalanch	e Energy	(Note 2)	8022	mJ	
I _{AR}	Avalanche Current (Note 1)		(Note 1)	76	Α	
E _{AR}	Repetitive Avalanche Energy (Note		(Note 1)	5.40	mJ	
dv/dt	MOSFET dv/dt Rugged	MOSFET dv/dt Ruggedness (Note 3)			V/ns	
αν/αι	Peak Diode Recovery d	v/dt		12	V/IIS	
D	Dower Dissination	(T _C = 25°C)		543	W	
P _D Power Dissipation	- Derate Above 25°C		5.40	W/°C		
T _J , T _{STG}	Operating and Storage Temperature Range			-55 to +150	°C	
TL	Maximum Lead Temper	ature for Soldering, 1/8" from Case for 5 Second	onds	300	°C	

Thermal Characteristics

Symbol	Parameter	FCA76N60N	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.23	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	tance, Junction to Ambient, Max. 40		

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCA76N60N	FCA76N60N	TO-3PN	Tube	N/A	N/A	30 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}, T_J = 25^{\circ}\text{C}$	600	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 1 mA, Referenced to 25°C	-	0.73	-	V/°C
_	Zero Gate Voltage Drain Current	V _{DS} = 480 V, V _{GS} = 0 V	-	-	10	
IDSS	Zero Gate voltage Drain Current	$V_{DS} = 480 \text{ V}, T_{J} = 125^{\circ}\text{C}$	-	-	100	μА
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ±30 V, V _{DS} = 0 V	-	-	±100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	2.0	-	4.0	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 38 A	-	28.5	36.0	mΩ
g _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 38 A	-	88	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 400 V V 0 V	-	9310	12385	pF
C _{oss}	Output Capacitance	V _{DS} = 100 V, V _{GS} = 0 V, f = 1 MHz		370	495	pF
C _{rss}	Reverse Transfer Capacitance		-\	3.1	5.0	pF
Coss	Output Capacitance	$V_{DS} = 380 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	- \	196	-	pF
C _{oss(eff.)}	Effective Output Capacitance	$V_{DS} = 0 \text{ V to } 380 \text{ V}, V_{GS} = 0 \text{ V}$	-	914	-	pF
Q _{g(tot)}	Total Gate Charge at 10V		-	218	285	nC
Q_{gs}	Gate to Source Gate Charge	$V_{DS} = 380 \text{ V}, I_{D} = 38 \text{ A},$	-	39	-	nC
Q_{gd}	Gate to Drain "Miller" Charge	V _{GS} = 10 V (Note 4)	-	66	-	nC
ESR	Equivalent Series Resistance (G-S)	f = 1 MHz	-	1.0	-	Ω

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		- /	34	78	ns
t _r	Turn-On Rise Time	$V_{DD} = 380 \text{ V}, I_D = 38 \text{ A},$	-/	24	58	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 10 V, R_G = 4.7 Ω	/-	235	480	ns
t _f	Turn-Off Fall Time	(Note 4)	/ · -	32	74	ns

Drain-Source Diode Characteristics

I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	76	Α
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	- ,	228	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 38 A	-	-	1.2	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 38 A,	-	613	-	ns
Q _{rr}	Reverse Recovery Charge	$dI_F/dt = 100 A/\mu s$	-	16	///-	μС

Notes:

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. I_AS = 25.3 A, R_G = 25 Ω , starting T_J = 25°C.
- 3. I $_{SD} \leq 76$ A, di/dt ≤ 200 A/µs, V $_{DD} \leq 380$ V, starting T $_{J}$ = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

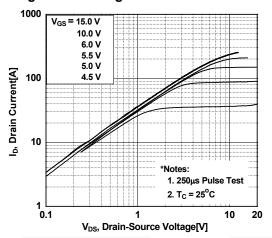


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

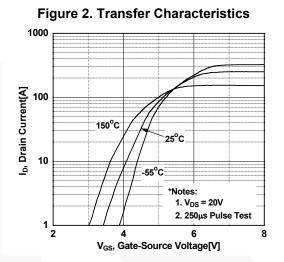


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

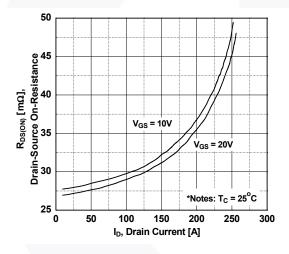
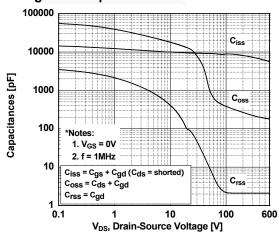


Figure 5. Capacitance Characteristics



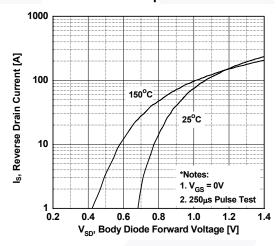
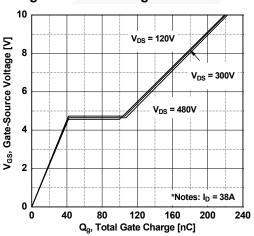


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

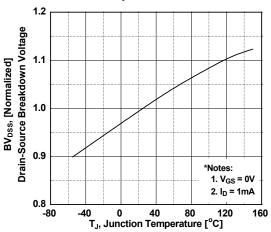


Figure 8. On-Resistance Variation vs. Temperature

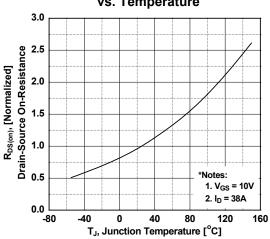


Figure 9. Maximum Safe Operating Area

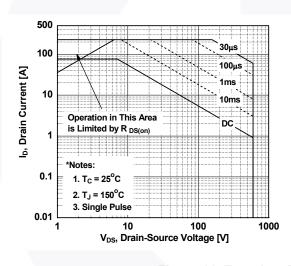


Figure 10. Maximum Drain Current vs. Case Temperature

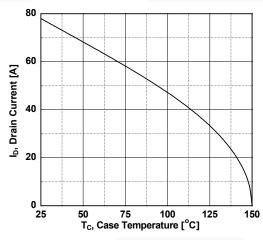
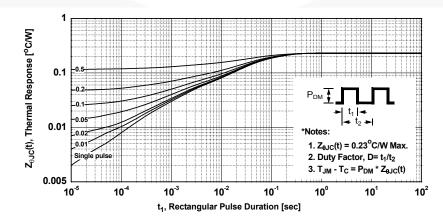


Figure 11. Transient Thermal Response Curve



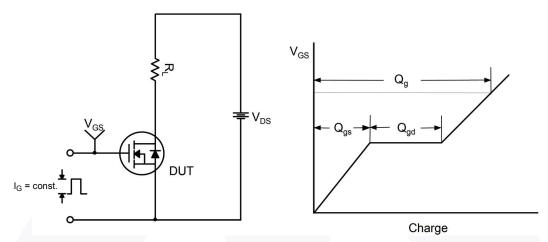


Figure 12. Gate Charge Test Circuit & Waveform

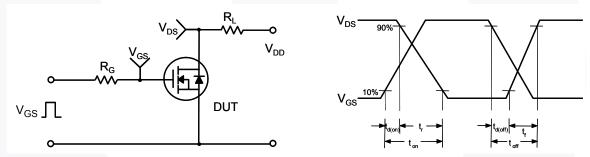


Figure 13. Resistive Switching Test Circuit & Waveforms

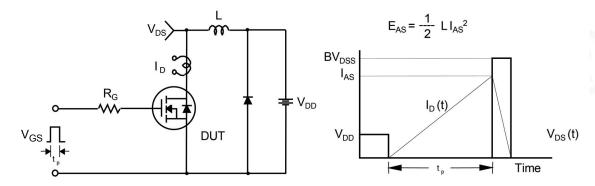


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

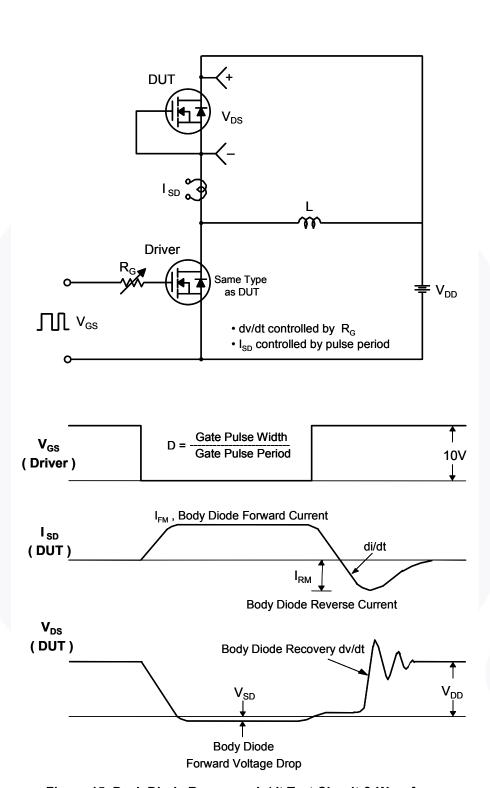
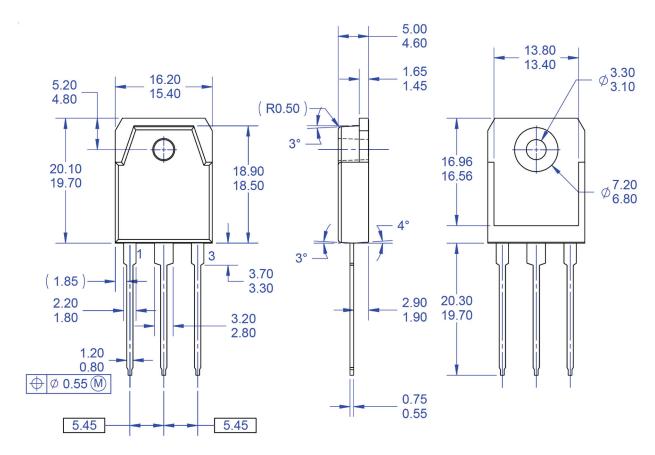


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions





NOTES: UNLESS OTHERWISE SPECIFIED

- A) THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD.

 B) ALL DIMENSIONS ARE IN MILLIMETERS.
 C) DIMENSION AND TOLERANCING PER ASME14.5-2009.

- D) DIMENSIONS ARE EXCLUSSIVE OF BURRS. MOLD FLASH, AND TIE BAR EXTRUSSIONS.
 DRAWING FILE NAME: TO3PN03AREV1.
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Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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